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2N5086/2N5087/MMBT5087

PNP General Purpose Amplifier

• This device is designed for low level, high gain, low noise general purpose amplifier applications at collector currents to 50mA.





1. Emitter 2. Base 3. Collector

1. Base 2. Emitter 3. Collector

Absolute Maximum Ratings* T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{CBO}	Collector-Base Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-3.0	V
I _C	Collector current - Continuous	-100	mA
T _J , T _{stg}	Junction and Storage Temperature	-55 ~ +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition		Min.	Max.	Units
Off Charac	teristics					
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage *	$I_C = -1.0 \text{mA}, I_B = 0$		-50		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = -100 \mu A, I_E = 0$		-50		V
I _{CEO}	Collector Cutoff Current	$V_{CB} = -10V, I_{E} = 0$			-10	nA
		$V_{CB} = -35V, I_{E} = 0$			-50	nA
I _{CBO}	Emitter Cutoff Current	$V_{EB} = -3.0V, I_{C} = 0$			-50	nA
On Charac	teristics					
h _{FE}	DC Current Gain	$I_C = -100 \mu A, V_{CE} = -5.0 V$	5086	150	500	
			5087	250	800	
		$I_C = -1.0 \text{mA}, V_{CE} = -5.0 \text{V}$	5086	150		
			5087	250		
		$I_C = -10 \text{mA}, V_{CE} = -5.0 \text{V}$	5086	150		
			5087	250		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -10 \text{mA}, I_B = -1.0 \text{mA}$			-0.3	V
V _{BE(on)}	Base-Emitter On Voltage	$I_C = -1.0 \text{mA}, V_{CE} = -5.0 \text{V}$			-0.85	V
	al Characteristics					
f _T	Current Gain Bandwidth Product	$I_C = -500\mu A$, $V_{CE} = -5.0V$, $f = 20MHz$		40		MHz
C _{cb}	Collector-Base Capacitance	$V_{CB} = -5.0V, I_{E} = 0, f = 100KHz$			4.0	pF
h _{fe}	Small-Signal Current Gain	$I_C = -1.0 \text{mA}, V_{CE} = -5.0 \text{V},$	5086	150	600	
		f = 1.0KHz	5087	250	900	
NF	Noise Figure	$I_C = -100 \mu A, V_{CE} = -5.0 V$	5086		3.0	dB
		$R_S = 3.0k\Omega$, $f = 1.0KHz$	5087		2.0	dB
		$I_C = -20\mu A$, $V_{CE} = -5.0V$	5086		3.0	dB
		$R_S = 10k\Omega$	5087		2.0	dB
		f = 10Hz to 15.7KHz				

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ınermai	Characteristics	T _a =25°C unless otherwise noted

		Ma			
Symbol	Parameter	2N5086 2N5087	*MMBT5087	Units	
P _D	Total Device Dissipation	625	350	mW	
	Derate above 25°C	5.0	2.8	mW/°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W	

^{*} Device mounted on FR-4 PCB 1.6" × 1.6" × 0.06."

Typical Characteristics

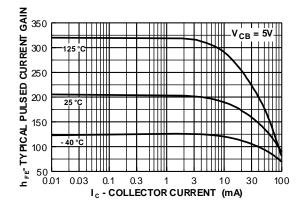


Figure 1. Typical Pulsed Current Gain vs Collector Current

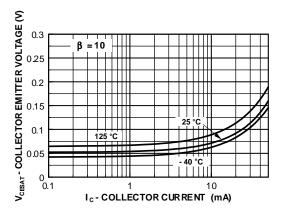


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

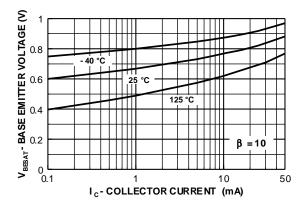


Figure 3. Base-Emitter Saturation Voltage vs Collector Current

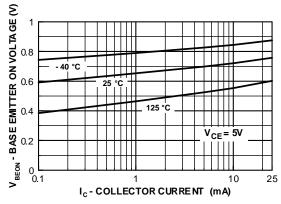


Figure 4. Base-Emitter On Voltage vs Collector Current

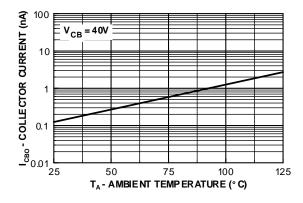


Figure 5. Collector Cutoff Current vs Ambient Temperature

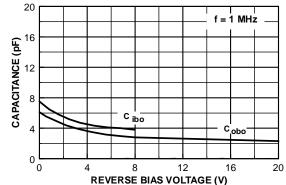


Figure 6. Input and Output Capacitance vs Reverse Voltag

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Typical Characteristics(Continuce)

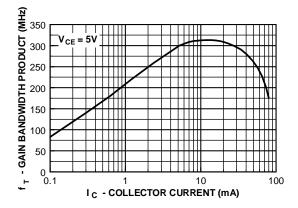


Figure 7. Gain Bandwidth Product vs Collector Current

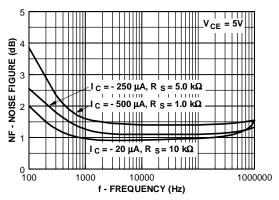


Figure 8. Noise Figure vs Frequency

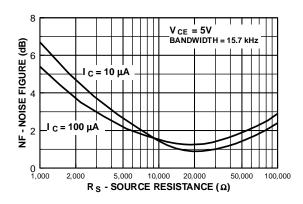


Figure 9. Wideband Noise Frequency vs Source Resistance

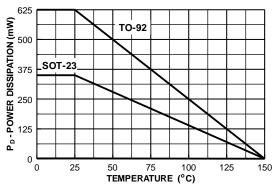


Figure 10. Power Dissipation vs Ambient Temperature

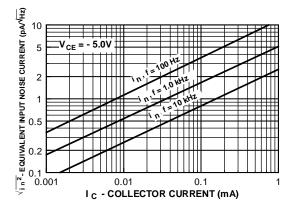


Figure 11. Equivalent Input Noise Current vs Collector Current

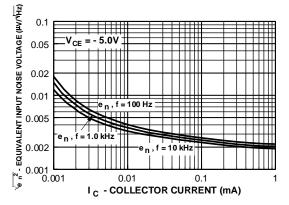


Figure 12. Equivalent Input Noise Voltage vs Collector Current

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Typical Characteristics (Continuce)

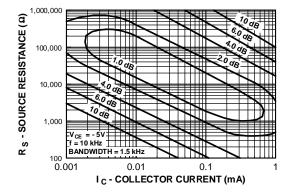


Figure 13. Contours of Constanct Narrow Band Noise Figure

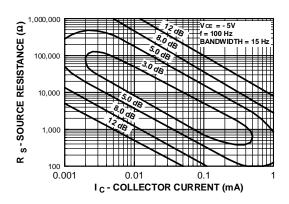


Figure 14. Contours of Constanct Narrow Band Noise Figure

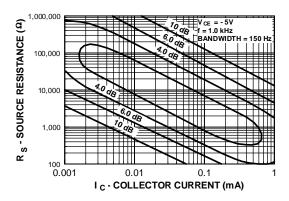


Figure 15. BContours of Constant Narrow Band Noise Figure

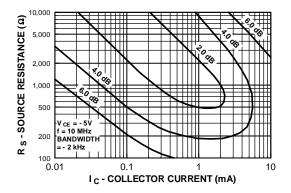
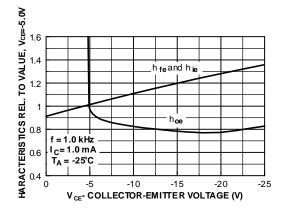
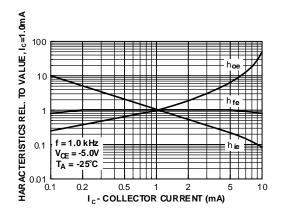


Figure 16. Contours of Constant Narrow Band Noisd Figure

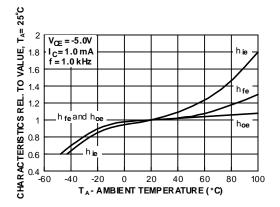
Typical Common Emitter Characteristics (f = 1.0KHz)



Typical Common Emitter Characteristics



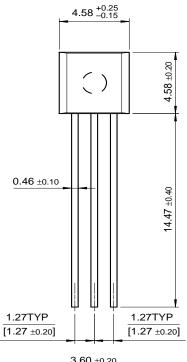
Typical Common Emitter Characteristics

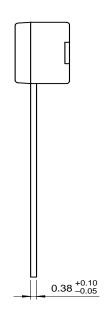


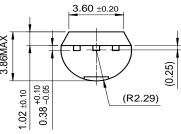
Typical Common Emitter Characteristics

Package Dimensions

TO-92

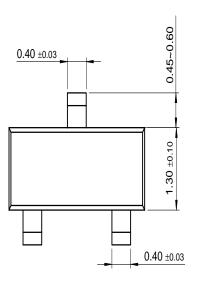


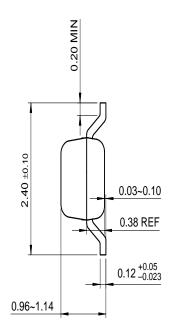


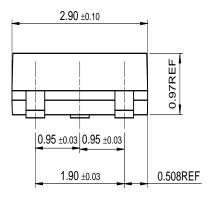


Package Dimensions (Continued)

SOT-23







Dimensions in Millimeters

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